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U.S. UTILITY Patent Application

PATENT NUMBER and
ISSUE DATE

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10041026	12/28/2001	118		1734	Meeky

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****CONTINUING DATA VERIFIED:**

**** FOREIGN APPLICATIONS VERIFIED:**

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO 006333
35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no		
Verified and Acknowledged Examiners's initials		
TITLE : Methods for silicon oxide and oxynitride deposition using single wafer low pressure CVD		

U.S. DEPT. OF COMM./PAT. & TM-PTO-436L (Rev. 12-94)

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G
Assistant Examiner		DRAWING	
ISSUE FEE		Sheets Drwg.	Figs. Drwg.
Amount Due	Date Paid	Print Fig.	
Primary Examiner		Application Examiner	
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE	
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